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(54) Title: HIGH SELECTIVITY, LOW STRESS, AND LOW HYDROGEN CARBON HARDMASKS IN LOW-PRESSURE CONDITIONS WITH WIDE GAP ELECTRODE SPACING

(57) Abstract: Provided herein are methods and related apparatus for de-
positing an ashable hard mask (AHM) on a substrate by providing a wide
gap electrode spacing in low-pressure conditions. A wide gap electrode may
facilitate control of parasitic plasmas in low-pressure conditions, thereby en-
abling formation of high selectivity, low stress, and low- hydrogen AHMs.
The AHM may then be used to etch features into underlying layers of the
substrate.

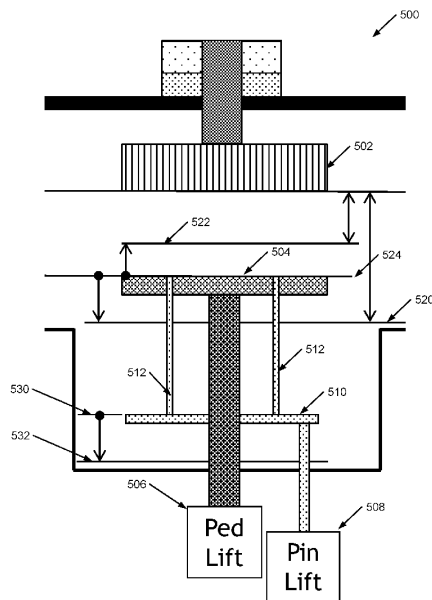


FIG. 5

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